

N - Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
30	21 at V _{GS} = 10 V	6	10.7 nC			
30	22 at V _{GS} = 4.5 V					

FEATURES

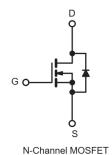
- DT-Trench MOSFET
- 100 % R_g and UIS Tested
- · Surface mount package
- · Lead free product is acquired



RoHS

APPLICATIONS

- PWM applications
- · Load switch



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D = 3	3
1	
G	S
Top View	/

(SOT-23-3L)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 25 °C	l _D	6	Α	
	T _C = 100 °C		3.7		
Pulsed Drain Current ^b		I _{DM}	20		
Maximum Power Dissipation ^c	T _C = 25 °C	Pn	1.7	W	
Maximum Fower Dissipation	T _C = 100 °C		0.68	VV	
Operating Junction and Storage Temperature R	ange	T _J , T _{stg}	- 55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	120	°C/W		
Junction-to-Case (Drain)	R _{thJC}	73.5	- *C/W		

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.





PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static			•	,			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0	-	3.0		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = 30 V, V _{GS} = 0 V		-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 V$, $V_{GS} = 5 V$	6	-	-	Α	
Drain-Source On-State Registance 8	Prov.	V _{GS} = 10 V, I _D = 3 A	-	21	24	m0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 3 \text{ A}$	-	22	33	- mΩ	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 3 \text{ A}$	-	13	-	S	
Dynamic ^b			•				
Input Capacitance	C _{iss}		-	457	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$	-	67	-		
Reverse Transfer Capacitance	C _{rss}		-	59	-		
Total Gate Charge ^c	Q_g		-	10.7	-		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$	-	0.75	-	nC	
Gate-Drain Charge ^c	Q _{gd}		-	2.25	-		
Gate Resistance	R_g	f = 1 MHz	-	4.8	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	4.5	-		
Rise Time ^c	t _r	$V_{DS} = 15 \text{ V}, I_{D} = 3 \text{ A}, R_{g} = 3 \Omega$	-	3	-		
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	15	-	ns	
Fall Time ^c	t _f		-	4	-		
Drain-Source Body Diode Ratings and	Characterist	cics b (T _C = 25 °C)					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	6	Α	
Pulsed Current (t = 100 μs)	I _{SM}		-	-	20	Α	
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1.2	V	
Reverse Recovery Time	t _{rr}	L = 3 A di/d+ = 100 A/via	-	9	-	ns	
Reverse Recovery Charge	Q _{rr}	$I_F = 3A$, di/dt = 100 A/ μ s	-	4	-	nC	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

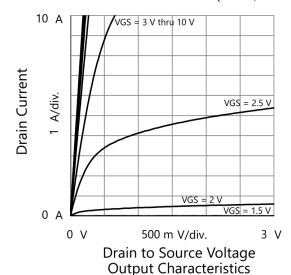
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

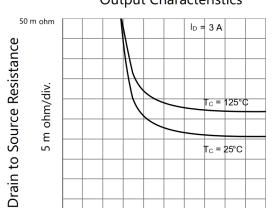


0 ohm

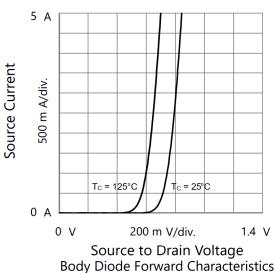
TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)

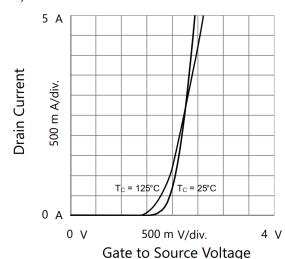
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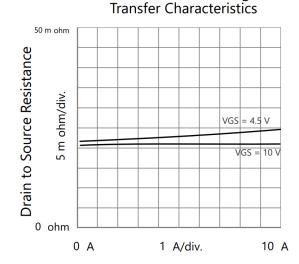


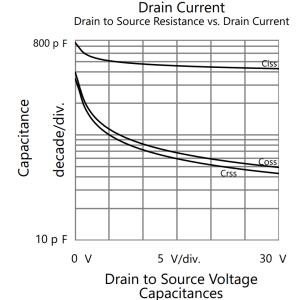


0 V 1 V/div. 10 V Gate to Source Voltage Drain to Source Resistance vs. Gate to Source Voltage

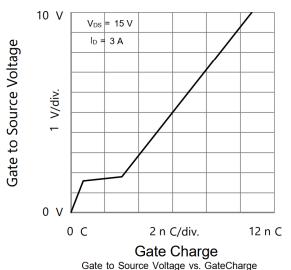


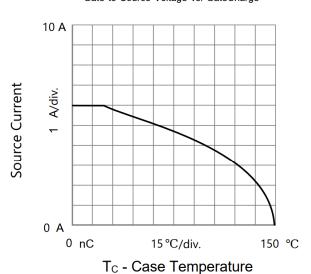




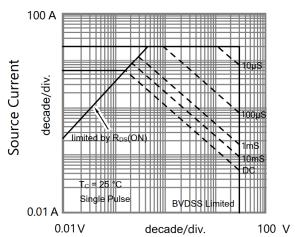


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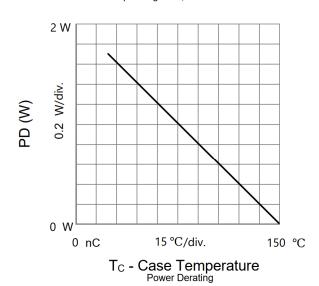


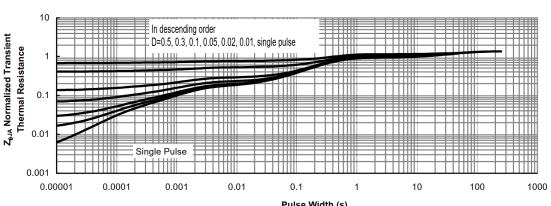


Current Derating



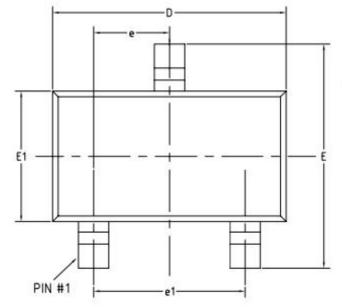
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient

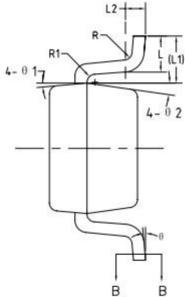


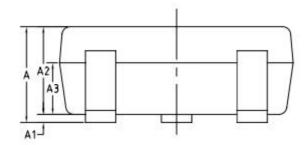


Pulse Width (s) Normalized Maximum Transient Thermal Impedance

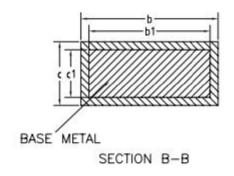
SOT-23-3L PACKAGE OUTLINE







COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)



SYMBOL	MIN	TYP	MAX
Α	-	-	1.50
A1	0.00	-	0.18
A2	0.85	1.10	1.35
A3	0.58	0.65	0.72
b	0.23	-	0.53
b1	0.20	0.40	0.50
С	0.09	-	0.22
c1	0.08	0.13	0.21
D	2.78	2.95	3.10
Е	2.58	2.80	3.03
E1	1.55	1.65	1.78
е	0.83	0.95	1.07
e1	1.78	1.90	2.02
L	0.28	0.45	0.62
L1	0.59REF		
L2	0.25BSC		
R	0.04	-	-
R1	0.04	-	0.21
θ	0°	-	8°
θ1	8°	10°	12°
θ2	8°	10°	12°





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